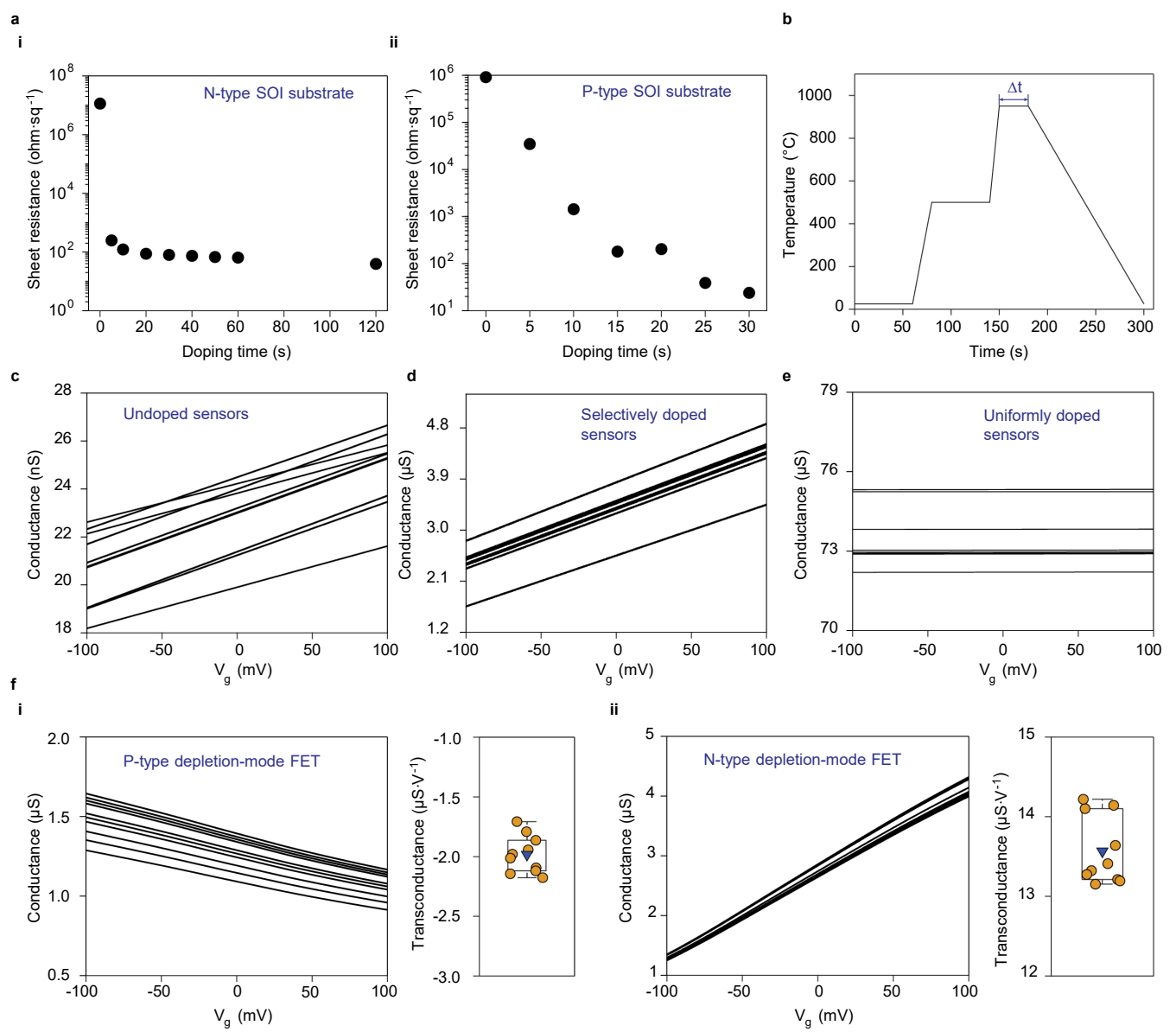
a
i
N-type SOI substrate
Sheet resistance (ohm·sq⁻¹)
Doping time (s)
ii
P-type SOI substrate
Sheet resistance (ohm·sq⁻¹)
Doping time (s)
b
Δt
Temperature (°C)
Time (s)
c
Undoped sensors
Conductance (nS)
V_g (mV)
d
Selectively doped sensors
Conductance (µS)
V_g (mV)
e
Uniformly doped sensors
Conductance (µS)
V_g (mV)

f
i
P-type depletion-mode FET
Conductance (µS)
V_g (mV)
Transconductance (µS·V⁻¹)
ii
N-type depletion-mode FET
Conductance (µS)
V_g (mV)
Transconductance (µS·V⁻¹)